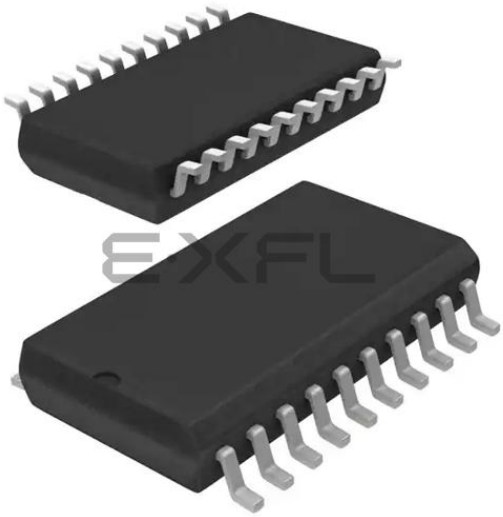

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What is "Embedded - Microcontrollers"?

"Embedded - Microcontrollers" refer to small, integrated circuits designed to perform specific tasks within larger systems. These microcontrollers are essentially compact computers on a single chip, containing a processor core, memory, and programmable input/output peripherals. They are called "embedded" because they are embedded within electronic devices to control various functions, rather than serving as standalone computers. Microcontrollers are crucial in modern electronics, providing the intelligence and control needed for a wide range of applications.

Applications of "Embedded - Microcontrollers"

Details	
Product Status	Obsolete
Core Processor	AVR
Core Size	8-Bit
Speed	4MHz
Connectivity	SPI, UART/USART
Peripherals	Brown-out Detect/Reset, POR, PWM, WDT
Number of I/O	15
Program Memory Size	2KB (1K x 16)
Program Memory Type	FLASH
EEPROM Size	128 x 8
RAM Size	128 x 8
Voltage - Supply (Vcc/Vdd)	2.7V ~ 6V
Data Converters	-
Oscillator Type	External
Operating Temperature	-40°C ~ 85°C
Mounting Type	Surface Mount
Package / Case	20-SOIC (0.295", 7.50mm Width)
Supplier Device Package	20-SOIC
Purchase URL	https://www.e-xfl.com/product-detail/microchip-technology/at90s2313-4si

selectable power-saving modes. The Idle mode stops the CPU while allowing the SRAM, Timer/Counters, SPI port and interrupt system to continue functioning. The Power-down mode saves the register contents but freezes the Oscillator, disabling all other chip functions until the next external interrupt or Hardware Reset.

The device is manufactured using Atmel's high-density non-volatile memory technology. The On-chip In-System Programmable Flash allows the Program memory to be reprogrammed in-system through an SPI serial interface or by a conventional non-volatile memory programmer. By combining an enhanced RISC 8-bit CPU with In-System Programmable Flash on a monolithic chip, the Atmel AT90S2313 is a powerful microcontroller that provides a highly flexible and cost-effective solution to many embedded control applications.

The AT90S2313 AVR is supported with a full suite of program and system development tools including: C compilers, macro assemblers, program debugger/simulators, In-Circuit Emulators and evaluation kits.

Pin Descriptions

VCC Supply voltage pin.

GND Ground pin.

Port B (PB7..PB0) Port B is an 8-bit bi-directional I/O port. Port pins can provide internal pull-up resistors (selected for each bit). PB0 and PB1 also serve as the positive input (AIN0) and the negative input (AIN1), respectively, of the On-chip Analog Comparator. The Port B output buffers can sink 20 mA and can drive LED displays directly. When pins PB0 to PB7 are used as inputs and are externally pulled low, they will source current if the internal pull-up resistors are activated. The Port B pins are tri-stated when a reset condition becomes active, even if the clock is not active.

Port B also serves the functions of various special features of the AT90S2313 as listed on page 51.

Port D (PD6..PD0) Port D has seven bi-directional I/O ports with internal pull-up resistors, PD6..PD0. The Port D output buffers can sink 20 mA. As inputs, Port D pins that are externally pulled low will source current if the pull-up resistors are activated. The Port D pins are tri-stated when a reset condition becomes active, even if the clock is not active.

Port D also serves the functions of various special features of the AT90S2313 as listed on page 56.

$\overline{\text{RESET}}$ Reset input. A low level on this pin for more than 50 ns will generate a Reset, even if the clock is not running. Shorter pulses are not guaranteed to generate a Reset.

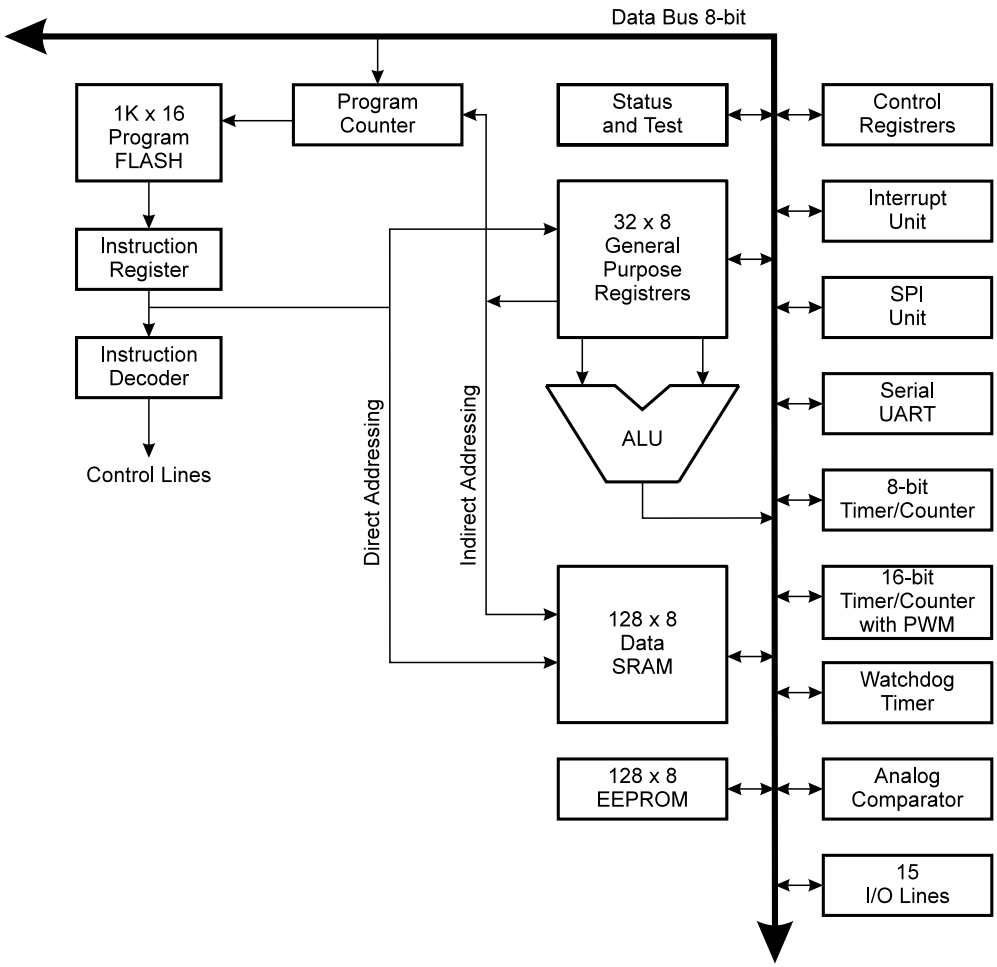
XTAL1 Input to the inverting Oscillator amplifier and input to the internal clock operating circuit.

XTAL2 Output from the inverting Oscillator amplifier.

Architectural Overview

The fast-access Register File concept contains 32 x 8-bit general purpose working registers with a single clock cycle access time. This means that during one single clock cycle, one ALU (Arithmetic Logic Unit) operation is executed. Two operands are output from the Register File, the operation is executed, and the result is stored back in the Register File – in one clock cycle.

Figure 4. The AT90S2313 AVR RISC Architecture



Six of the 32 registers can be used as three 16-bit indirect address register pointers for Data Space addressing – enabling efficient address calculations. One of the three address pointers is also used as the address pointer for the constant table look-up function. These added function registers are the 16-bit X-register, Y-register, and Z-register.

The ALU supports arithmetic and logic functions between registers or between a constant and a register. Single register operations are also executed in the ALU. Figure 4 shows the AT90S2313 AVR RISC microcontroller architecture.

In addition to the register operation, the conventional memory addressing modes can be used on the Register File as well. This is enabled by the fact that the Register File is assigned the 32 lowermost Data Space addresses ($00 - $1F), allowing them to be accessed as though they were ordinary memory locations.

The I/O memory space contains 64 addresses for CPU peripheral functions such as control registers, Timer/Counters, A/D converters and other I/O functions. The I/O memory can be accessed directly or as the Data Space locations following those of the Register File, $20 - $5F.

The AVR has Harvard architecture – with separate memories and buses for program and data. The program memory is accessed with a 2-stage pipeline. While one instruction is being executed, the next instruction is pre-fetched from the program memory. This concept enables instructions to be executed in every clock cycle. The program memory is In-System Programmable Flash memory.

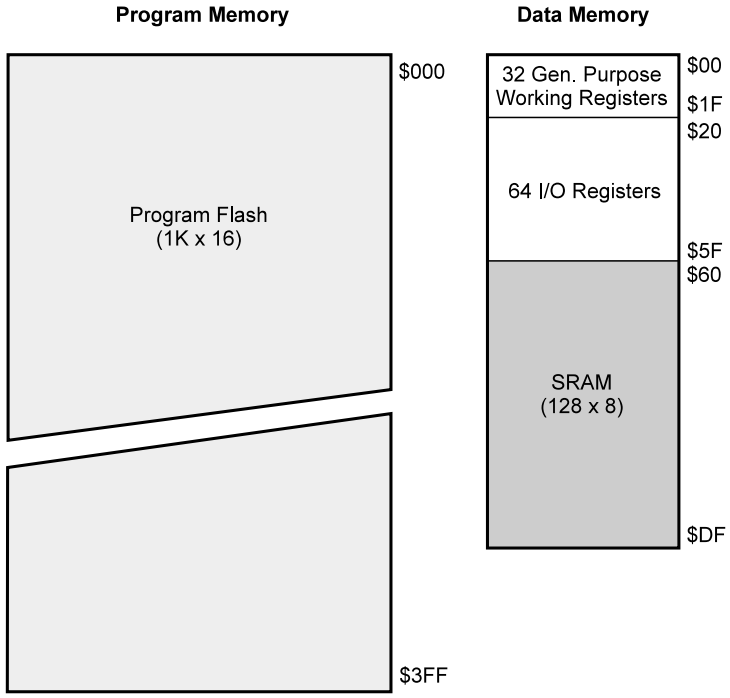
With the relative jump and call instructions, the whole 1K address space is directly accessed. Most AVR instructions have a single 16-bit word format. Every program memory address contains a 16- or 32-bit instruction.

During interrupts and subroutine calls, the return address Program Counter (PC) is stored on the Stack. The Stack is effectively allocated in the general data SRAM, and consequently the stack size is only limited by the total SRAM size and the usage of the SRAM. All user programs must initialize the SP in the reset routine (before subroutines or interrupts are executed). The 8-bit Stack Pointer (SP) is read/write accessible in the I/O space.

The 128 bytes data SRAM + Register File and I/O Registers can be easily accessed through the five different addressing modes supported in the AVR architecture.

The memory spaces in the AVR architecture are all linear and regular memory maps.

Figure 5. Memory Maps



A flexible interrupt module has its control registers in the I/O space with an additional Global Interrupt Enable bit in the Status Register. All the different interrupts have a separate Interrupt Vector in the Interrupt Vector table at the beginning of the program memory. The different interrupts have priority in accordance with their Interrupt Vector position. The lower the Interrupt Vector address, the higher the priority.

General Interrupt FLAG Register – GIFR

Bit	7	6	5	4	3	2	1	0	
$3A ($5A)	INTF1	INTF0	–	–	–	–	–	–	GIFR
Read/Write	R/W	R/W	R	R	R	R	R	R	
Initial value	0	0	0	0	0	0	0	0	

• Bit 7 – INTF1: External Interrupt Flag1

When an edge on the INT1 pin triggers an interrupt request, the corresponding Interrupt Flag, INTF1, becomes set (one). If the I-bit in SREG and the corresponding interrupt enable bit, INT1 bit in GIMSK, are set (one), the MCU will jump to the Interrupt Vector. The flag is cleared when the interrupt routine is executed. Alternatively, the flag can be cleared by writing a logical “1” to it. The flag is always cleared when INT1 is configured as level interrupt.

• Bit 6 – INTF0: External Interrupt Flag0

When an edge on the INT0 pin triggers an interrupt request, the corresponding Interrupt Flag, INTF0, becomes set (one). If the I-bit in SREG and the corresponding interrupt enable bit, INT0 bit in GIMSK, are set (one), the MCU will jump to the Interrupt Vector. The flag is cleared when the interrupt routine is executed. Alternatively, the flag can be cleared by writing a logical “1” to it. The flag is always cleared when INT0 is configured as level interrupt.

• Bits 5..0 – Res: Reserved Bits

These bits are reserved bits in the AT90S2313 and always read as zero.

Note that external level interrupt does not have a flag, and will only be remembered for as long as the interrupt condition is active.

Timer/Counter Interrupt Mask Register – TIMSK

Bit	7	6	5	4	3	2	1	0	
$39 ($59)	TOIE1	OCIE1A	–	–	TICIE1	–	TOIE0	–	TIMSK
Read/Write	R/W	R/W	R	R	R/W	R	R/W	R	
Initial value	0	0	0	0	0	0	0	0	

• Bit 7 – TOIE1: Timer/Counter1 Overflow Interrupt Enable

When the TOIE1 bit is set (one) and the I-bit in the Status Register is set (one), the Timer/Counter1 Overflow Interrupt is enabled. The corresponding interrupt (at vector $005) is executed if an overflow in Timer/Counter1 occurs (i.e., when the TOV1 bit is set in the Timer/Counter Interrupt Flag Register [TIFR]).

• Bit 6 – OCIE1A: Timer/Counter1 Output Compare Match Interrupt Enable

When the OCIE1A bit is set (one) and the I-bit in the Status Register is set (one), the Timer/Counter1 Compare Match Interrupt is enabled. The corresponding interrupt (at vector $004) is executed if a compare match in Timer/Counter1 occurs (i.e., when the OCF1A bit is set in the Timer/Counter Interrupt Flag Register [TIFR]).

• Bit 5,4 – Res: Reserved Bits

These bits are reserved bits in the AT90S2313 and always read as zero.

• Bit 4 – SM: Sleep Mode

This bit selects between the two available sleep modes. When SM is cleared (zero), Idle mode is selected as sleep mode. When SM is set (one), Power-down mode is selected as sleep mode. For details, refer to the paragraph “Sleep Modes”.

• Bits 3, 2 – ISC11, ISC10: Interrupt Sense Control 1 Bit 1 and Bit 0

The External Interrupt 1 is activated by the external pin INT1 if the SREG I-flag and the corresponding interrupt mask in the GIMSK Register is set. The level and edges on the external INT1 pin that activate the interrupt are defined in Table 5.

Table 5. Interrupt 1 Sense Control

ISC11	ISC10	Description
0	0	The low level of INT1 generates an interrupt request.
0	1	Reserved
1	0	The falling edge of INT1 generates an interrupt request.
1	1	The rising edge of INT1 generates an interrupt request.

• Bits 1, 0 – ISC01, ISC00: Interrupt Sense Control 0 Bit 1 and Bit 0

The External Interrupt 0 is activated by the external pin INT0 if the SREG I-flag and the corresponding interrupt mask is set. The level and edges on the external INT0 pin that activate the interrupt are defined in Table 6.

Table 6. Interrupt 0 Sense Control

ISC01	ISC00	Description
0	0	The low level of INT0 generates an interrupt request.
0	1	Reserved
1	0	The falling edge of INT0 generates an interrupt request.
1	1	The rising edge of INT0 generates an interrupt request.

The value on the INTn pin is sampled before detecting edges. If edge interrupt is selected, pulses with a duration longer than one CPU clock period will generate an interrupt. Shorter pulses are not guaranteed to generate an interrupt. If low-level interrupt is selected, the low level must be held until the completion of the currently executing instruction to generate an interrupt. If enabled, a level-triggered interrupt will generate an interrupt request as long as the pin is held low.

EEPROM Read/Write Access

The EEPROM Access Registers are accessible in the I/O space.

The write access time is in the range of 2.5 - 4 ms, depending on the V_{CC} voltages. A self-timing function, however, lets the user software detect when the next byte can be written. If the user code contains code that writes the EEPROM, some precaution must be taken. In heavily filtered power supplies, V_{CC} is likely to rise or fall slowly on Power-up/down. This causes the device for some period of time to run at a voltage lower than specified as minimum for the clock frequency used. CPU operation under these conditions may cause the Program Counter to perform unintentional jumps and eventually execute the EEPROM write code. To secure EEPROM integrity, the user is advised to use an external under-voltage reset circuit in this case.

In order to prevent unintentional EEPROM writes, a specific write procedure must be followed. Refer to the description of the EEPROM Control Register for details on this.

When the EEPROM is written, the CPU is halted for two clock cycles before the next instruction is executed. When the EEPROM is read, the CPU is halted for four clock cycles before the next instruction is executed.

EEPROM Address Register – EEAR

Bit	7	6	5	4	3	2	1	0	
$1E ($3E)	–	EEAR6	EEAR5	EEAR4	EEAR3	EEAR2	EEAR1	EEAR0	EEAR
Read/Write	R	R/W	R/W	R/W	R/W	R/W	R/W	R/W	
Initial value	0	0	0	0	0	0	0	0	

• Bit 7 – Res: Reserved Bit

This bit is a reserved bit in the AT90S2313 and will always read as zero.

• Bit 6..0 – EEAR6..0: EEPROM Address

The EEPROM Address Register (EEAR6..0) specifies the EEPROM address in the 128 bytes EEPROM space. The EEPROM data bytes are addressed linearly between 0 and 127.

EEPROM Data Register – EEDR

Bit	7	6	5	4	3	2	1	0	
$1D ($3D)	MSB							LSB	EEDR
Read/Write	R/W	R/W	R/W	R/W	R/W	R/W	R/W	R/W	
Initial value	0	0	0	0	0	0	0	0	

• Bit 7..0 – EEDR7..0: EEPROM Data

For the EEPROM write operation, the EEDR Register contains the data to be written to the EEPROM in the address given by the EEAR Register. For the EEPROM read operation, the EEDR contains the data read out from the EEPROM at the address given by EEAR.

Prevent EEPROM Corruption

During periods of low V_{CC}, the EEPROM data can be corrupted because the supply voltage is too low for the CPU and the EEPROM to operate properly. These issues are the same as for board-level systems using the EEPROM, and the same design solutions should be applied.

An EEPROM data corruption can be caused by two situations when the voltage is too low. First, a regular write sequence to the EEPROM requires a minimum voltage to operate correctly. Secondly, the CPU itself can execute instructions incorrectly if the supply voltage for executing instructions is too low.

EEPROM data corruption can easily be avoided by following these design recommendations (one is sufficient):

1. Keep the AVR RESET active (low) during periods of insufficient power supply voltage. This is best done by an external low V_{CC} Reset Protection circuit, often referred to as a Brown-out Detector (BOD). Please refer to the AVR 180 application note for design considerations regarding Power-on Reset and low-voltage detection.
2. Keep the AVR core in Power-down sleep mode during periods of low V_{CC}. This will prevent the CPU from attempting to decode and execute instructions, effectively protecting the EEPROM Registers from unintentional writes.
3. Store constants in Flash memory if the ability to change memory contents from software is not required. Flash memory cannot be updated by the CPU and will not be subject to corruption.

Port B Schematics

Note that all port pins are synchronized. The synchronization latches are, however, not shown in the figures.

Figure 38. Port B Schematic Diagram (Pins PB0 and PB1)

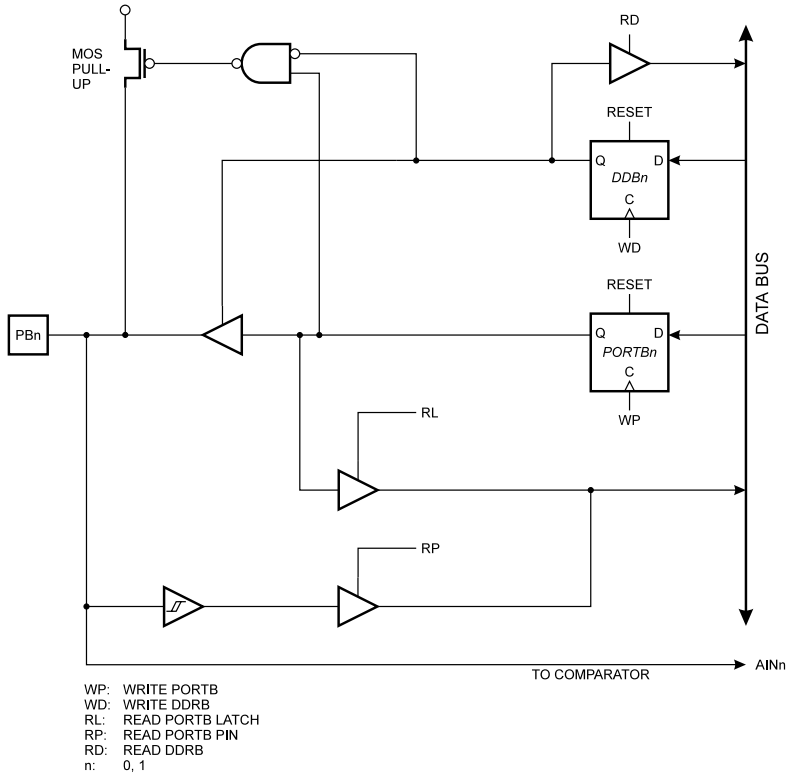


Figure 39. Port B Schematic Diagram (Pin PB3)

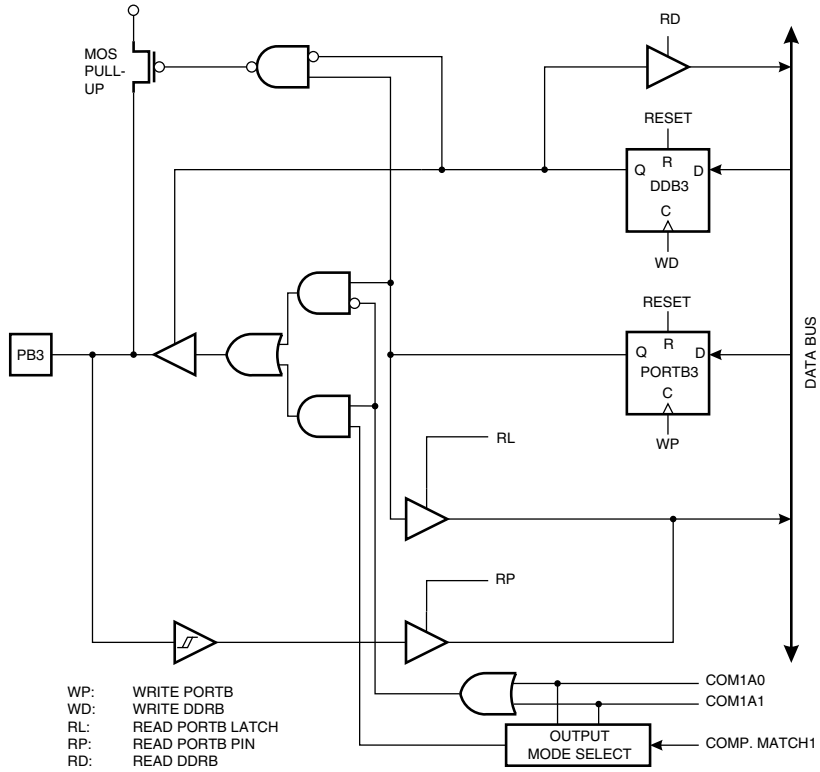


Figure 40. Port B Schematic Diagram (Pins PB2 and PB4)

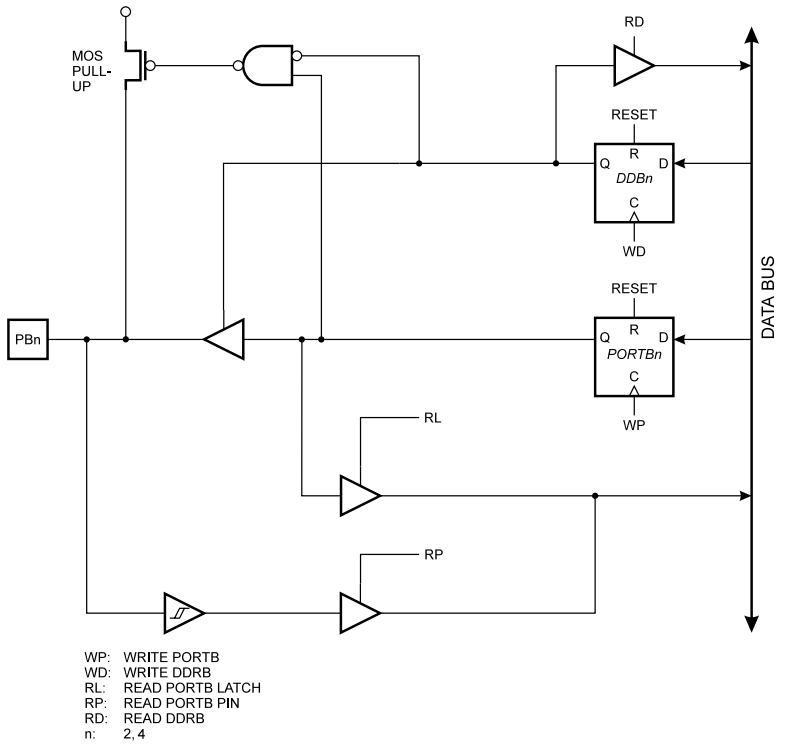


Figure 41. Port B Schematic Diagram (Pin PB5)

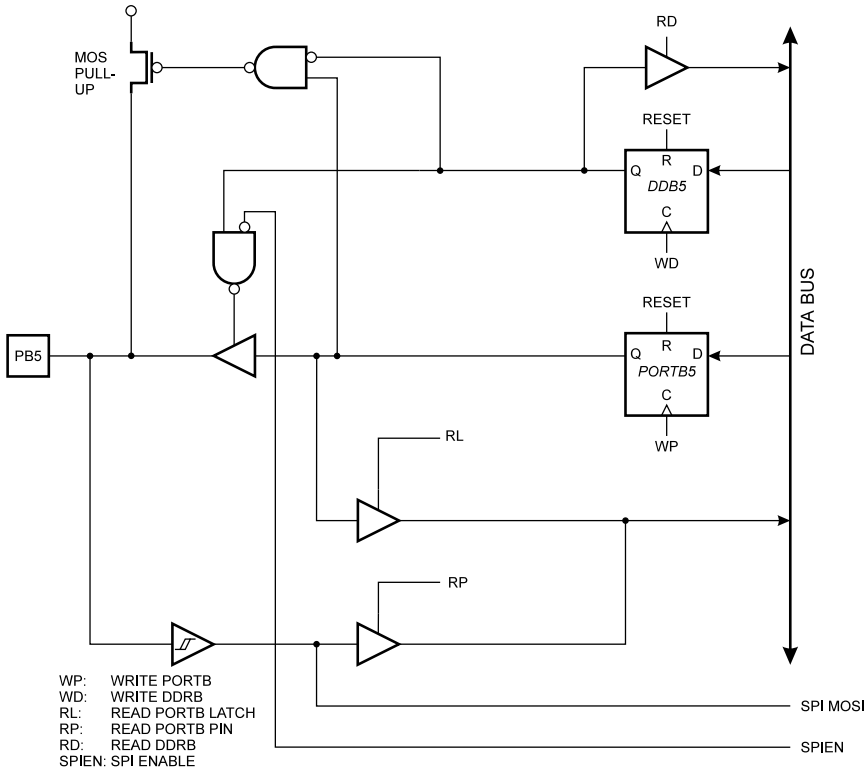


Figure 42. Port B Schematic Diagram (Pin PB6)

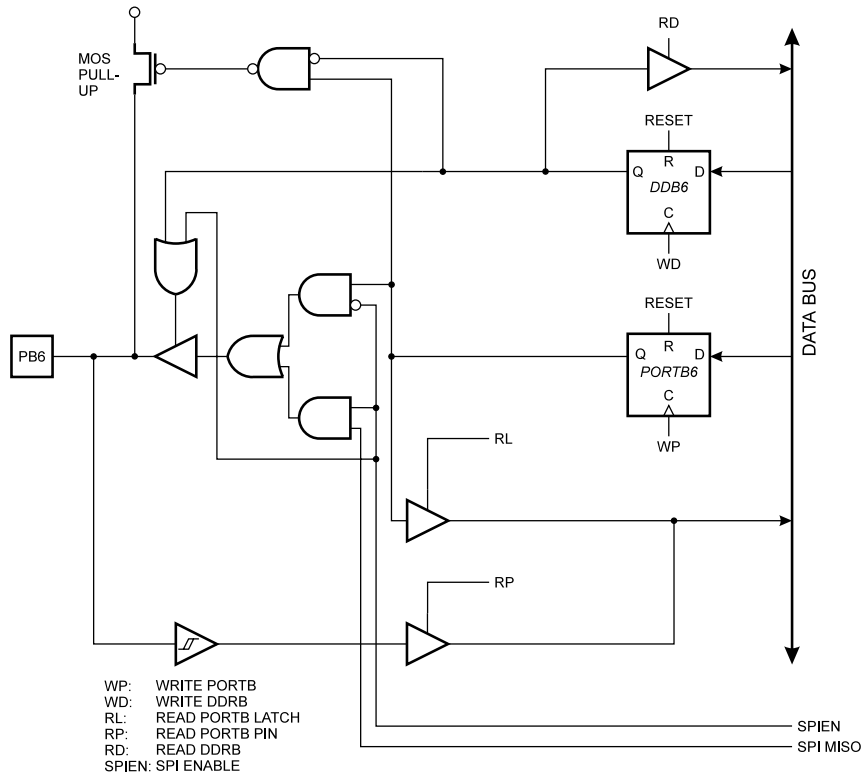


Table 23. Pin Name Mapping

Signal Name in Programming Mode	Pin Name	I/O	Function
XA0	PD5	I	XTAL Action Bit 0
XA1	PD6	I	XTAL Action Bit 1
DATA	PB7 - 0	I/O	Bi-directional Data Bus (Output when $\overline{OE}$ is low)

Table 24. XA1 and XA0 Coding

XA1	XA0	Action when XTAL1 is Pulsed
0	0	Load Flash or EEPROM Address (High or low address byte determined by BS)
0	1	Load Data (High or Low data byte for Flash determined by BS)
1	0	Load Command
1	1	No Action, Idle

Table 25. Command Byte Bit Coding

Command Byte	Command Executed
1000 0000	Chip Erase
0100 0000	Write Fuse Bits
0010 0000	Write Lock Bits
0001 0000	Write Flash
0001 0001	Write EEPROM
0000 1000	Read Signature Bytes
0000 0100	Read Fuse and Lock Bits
0000 0010	Read Flash
0000 0011	Read EEPROM

Enter Programming Mode

The following algorithm puts the device in Parallel Programming mode:

1. Apply supply voltage according to Table 22, between V_{CC} and GND.
2. Set the $\overline{RESET}$ and BS pin to “0” and wait at least 100 ns.
3. Apply 11.5 - 12.5V to $\overline{RESET}$. Any activity on BS within 100 ns after +12V has been applied to $\overline{RESET}$, will cause the device to fail entering Programming mode.

Chip Erase

The Chip Erase command will erase the Flash and EEPROM memories, and the Lock bits. The Lock bits are not reset until the Flash and EEPROM have been completely erased. The Fuse bits are not changed. Chip Erase must be performed before the Flash or EEPROM is reprogrammed.

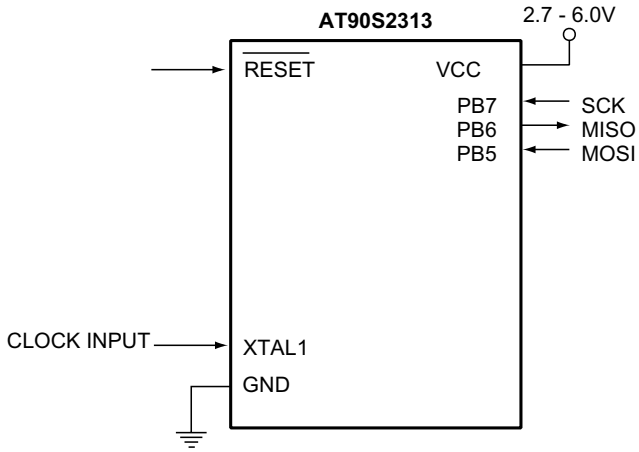
Load Command “Chip Erase”

1. Set XA1, XA0 to “10”. This enables command loading.
2. Set BS to “0”.
3. Set DATA to “1000 0000”. This is the command for Chip Erase.
4. Give XTAL1 a positive pulse. This loads the command.

Serial Downloading

Both the program and data memory arrays can be programmed using the serial SPI bus while $\overline{\text{RESET}}$ is pulled to GND. The serial interface consists of pins SCK, MOSI (input) and MISO (output). See Figure 53. After $\overline{\text{RESET}}$ is set low, the Programming Enable instruction needs to be executed first before program/erase instructions can be executed.

Figure 53. Serial Programming and Verify



For the EEPROM, an auto-erase cycle is provided within the self-timed write instruction and there is no need to first execute the Chip Erase instruction. The Chip Erase instruction turns the content of every memory location in both the program and EEPROM arrays into $FF.

The program and EEPROM memory arrays have separate address spaces: $0000 to $03FF for program Flash memory and $000 to $07F for EEPROM data memory.

Either an external clock is supplied at pin XTAL1 or a crystal needs to be connected across pins XTAL1 and XTAL2. The minimum low and high periods for the serial clock (SCK) input are defined as follows:

Low: > 2 XTAL1 clock cycle

High: > 2 XTAL1 clock cycles

Serial Programming Algorithm

When writing serial data to the AT90S2313, data is clocked on the rising edge of SCK.

When reading data from the AT90S2313, data is clocked on the falling edge of SCK. See Figure 54, Figure and Table 29 for timing details.

To program and verify the AT90S2313 in the Serial Programming mode, the following sequence is recommended (See 4-byte instruction formats in Table 28):

1. Power-up sequence:

   Apply power between V_{CC} and GND while $\overline{\text{RESET}}$ and SCK are set to “0”. If a crystal is not connected across pins XTAL1 and XTAL2, apply a clock signal to the XTAL1 pin. In some systems, the programmer cannot guarantee that SCK is held low during Power-up. In this case, $\overline{\text{RESET}}$ must be given a positive pulse of at least two XTAL1 cycles duration after SCK has been set to “0”.
2. Wait for at least 20 ms and enable serial programming by sending the Programming Enable serial instruction to the MOSI (PB5) pin.
3. The serial programming instructions will not work if the communication is out of synchronization. When in sync, the second byte ($53) will echo back when issu-

Serial Programming Characteristics

Figure 55. Serial Programming Timing

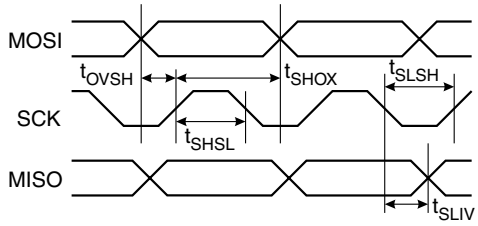


Table 29. Serial Programming Characteristics, T_A = -40°C to 85°C, V_{CC} = 2.7 - 6.0V (unless otherwise noted)

Symbol	Parameter	Min	Typ	Max	Units
$1/t_{CLCL}$	Oscillator Frequency (V_{CC} = 2.7 - 6.0V)	0		4.0	MHz
t_{CLCL}	Oscillator Period (V_{CC} = 2.7 - 6.0V)	250.0			ns
$1/t_{CLCL}$	Oscillator Frequency (V_{CC} = 4.0 - 6.0V)	0		10.0	MHz
t_{CLCL}	Oscillator Period (V_{CC} = 4.0 - 6.0V)	100.0			ns
t_{SHSL}	SCK Pulse Width High	2.0 t_{CLCL}			ns
t_{SLSH}	SCK Pulse Width Low	2.0 t_{CLCL}			ns
t_{OVSH}	MOSI Setup to SCK High	t_{CLCL}			ns
t_{SHOX}	MOSI Hold after SCK High	2.0 t_{CLCL}			ns
t_{SLIV}	SCK Low to MISO Valid	10.0	16.0	32.0	ns

Table 30. Minimum Wait Delay after the Chip Erase Instruction

Symbol	3.2V	3.6V	4.0V	5.0V
t_{WD_ERASE}	18 ms	14 ms	12 ms	8 ms

Table 31. Minimum Wait Delay after Writing a Flash or EEPROM Location

Symbol	3.2V	3.6V	4.0V	5.0V
t_{WD_PROG}	9 ms	7 ms	6 ms	4 ms

Typical Characteristics

The following charts show typical behavior. These figures are not tested during manufacturing. All current consumption measurements are performed with all I/O pins configured as inputs and with internal pull-ups enabled. A sine wave generator with rail-to-rail output is used as clock source.

The power consumption in Power-down mode is independent of clock selection.

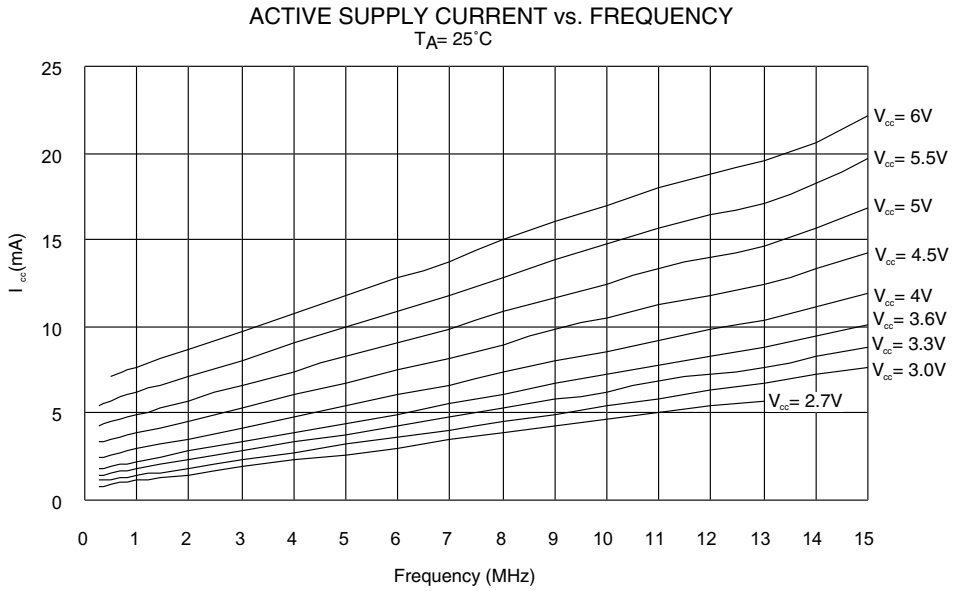
The current consumption is a function of several factors such as: operating voltage, operating frequency, loading of I/O pins, switching rate of I/O pins, code executed and ambient temperature. The dominating factors are operating voltage and frequency.

The current drawn from capacitive loaded pins may be estimated (for one pin) as $C_L \bullet V_{CC} \bullet f$ where C_L = load capacitance, V_{CC} = operating voltage and f = average switching frequency of I/O pin.

The parts are characterized at frequencies higher than test limits. Parts are not guaranteed to function properly at frequencies higher than the ordering code indicates.

The difference between current consumption in Power-down mode with Watchdog Timer enabled and Power-down mode with Watchdog Timer disabled represents the differential current drawn by the Watchdog Timer.

Figure 57. Active Supply Current vs. Frequency



Note: Analog Comparator offset voltage is measured as absolute offset.

Figure 64. Analog Comparator Offset Voltage vs. Common Mode Voltage

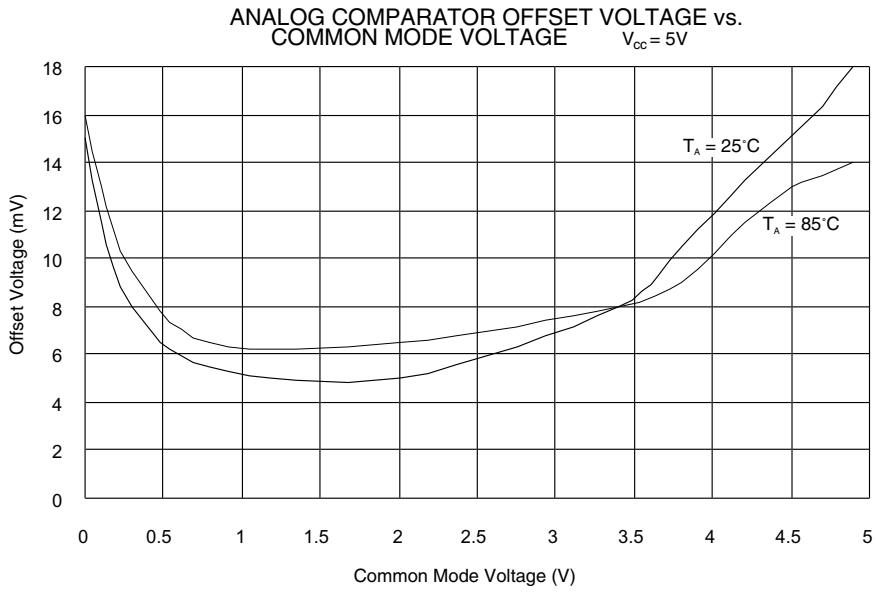


Figure 65. Analog Comparator Offset Voltage vs. Common Mode Voltage

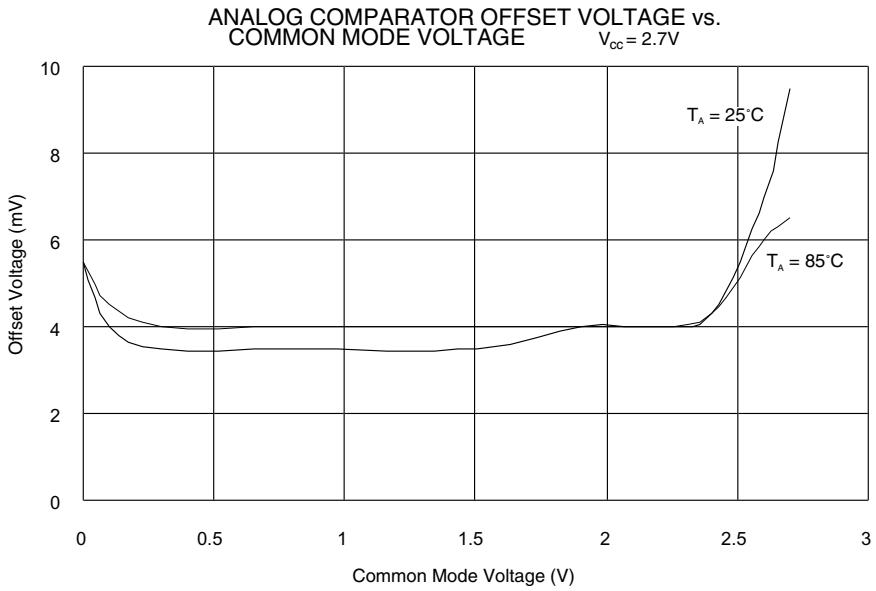


Figure 66. Analog Comparator Input Leakage Current

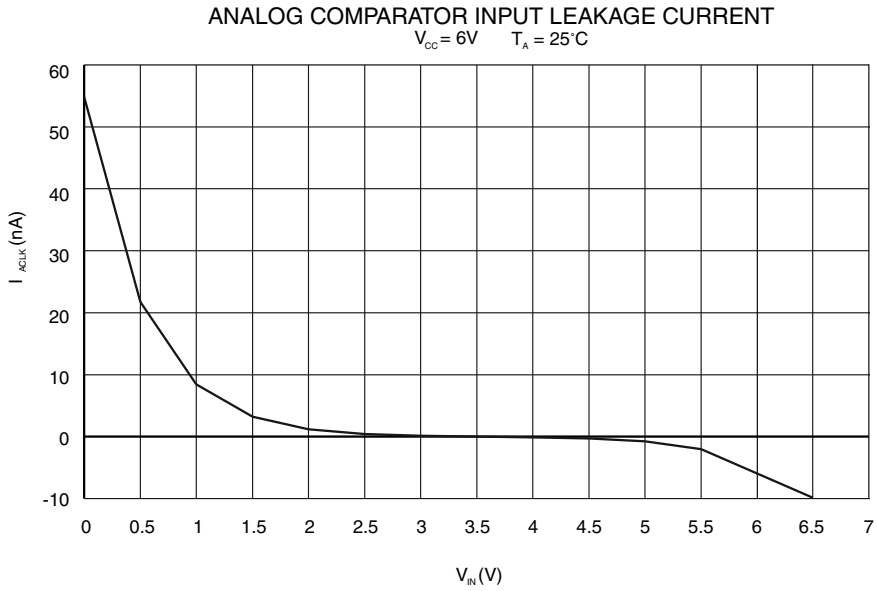
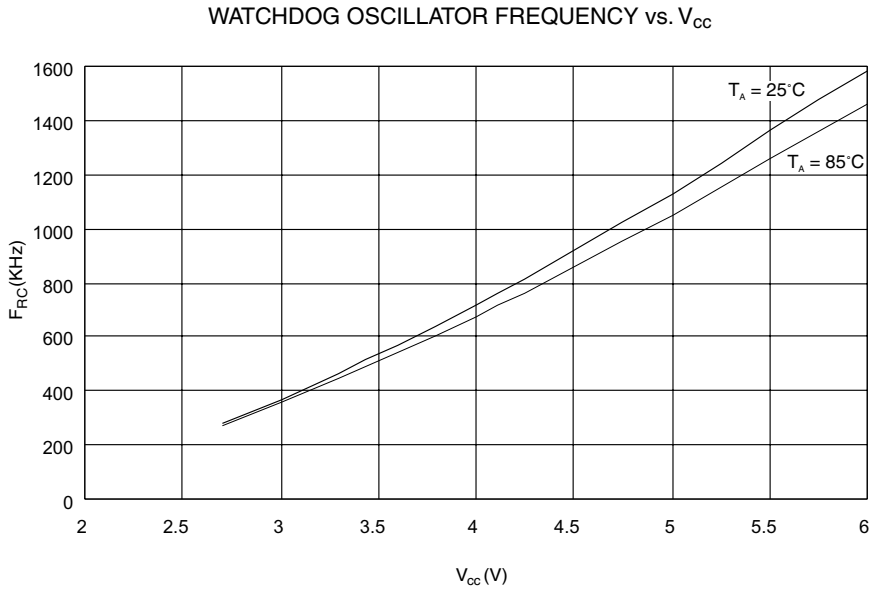


Figure 67. Watchdog Oscillator Frequency vs. V_{CC}



Instruction Set Summary (Continued)

Mnemonic	Operands	Description	Operation	Flags	# Clocks
DATA TRANSFER INSTRUCTIONS					
MOV	Rd, Rr	Move between Registers	Rd ← Rr	None	1
LDI	Rd, K	Load Immediate	Rd ← K	None	1
LD	Rd, X	Load Indirect	Rd ← (X)	None	2
LD	Rd, X+	Load Indirect and Post-Inc.	Rd ← (X), X ← X + 1	None	2
LD	Rd, -X	Load Indirect and Pre-Dec.	X ← X – 1, Rd ← (X)	None	2
LD	Rd, Y	Load Indirect	Rd ← (Y)	None	2
LD	Rd, Y+	Load Indirect and Post-Inc.	Rd ← (Y), Y ← Y + 1	None	2
LD	Rd, -Y	Load Indirect and Pre-Dec.	Y ← Y – 1, Rd ← (Y)	None	2
LDD	Rd, Y+q	Load Indirect with Displacement	Rd ← (Y + q)	None	2
LD	Rd, Z	Load Indirect	Rd ← (Z)	None	2
LD	Rd, Z+	Load Indirect and Post-Inc.	Rd ← (Z), Z ← Z+1	None	2
LD	Rd, -Z	Load Indirect and Pre-Dec.	Z ← Z - 1, Rd ← (Z)	None	2
LDD	Rd, Z+q	Load Indirect with Displacement	Rd ← (Z + q)	None	2
LDS	Rd, k	Load Direct from SRAM	Rd ← (k)	None	2
ST	X, Rr	Store Indirect	(X) ← Rr	None	2
ST	X+, Rr	Store Indirect and Post-Inc.	(X) ← Rr, X ← X + 1	None	2
ST	-X, Rr	Store Indirect and Pre-Dec.	X ← X - 1, (X) ← Rr	None	2
ST	Y, Rr	Store Indirect	(Y) ← Rr	None	2
ST	Y+, Rr	Store Indirect and Post-Inc.	(Y) ← Rr, Y ← Y + 1	None	2
ST	-Y, Rr	Store Indirect and Pre-Dec.	Y ← Y - 1, (Y) ← Rr	None	2
STD	Y+q, Rr	Store Indirect with Displacement	(Y + q) ← Rr	None	2
ST	Z, Rr	Store Indirect	(Z) ← Rr	None	2
ST	Z+, Rr	Store Indirect and Post-Inc.	(Z) ← Rr, Z ← Z + 1	None	2
ST	-Z, Rr	Store Indirect and Pre-Dec.	Z ← Z - 1, (Z) ← Rr	None	2
STD	Z+q, Rr	Store Indirect with Displacement	(Z + q) ← Rr	None	2
STS	k, Rr	Store Direct to SRAM	(k) ← Rr	None	2
LPM		Load Program Memory	R0 ← (Z)	None	3
IN	Rd, P	In Port	Rd ← P	None	1
OUT	P, Rr	Out Port	P ← Rr	None	1
PUSH	Rr	Push Register on Stack	STACK ← Rr	None	2
POP	Rd	Pop Register from Stack	Rd ← STACK	None	2
BIT AND BIT-TEST INSTRUCTIONS					
SBI	P, b	Set Bit in I/O Register	I/O(P,b) ← 1	None	2
CBI	P, b	Clear Bit in I/O Register	I/O(P,b) ← 0	None	2
LSL	Rd	Logical Shift Left	Rd(n+1) ← Rd(n), Rd(0) ← 0	Z,C,N,V	1
LSR	Rd	Logical Shift Right	Rd(n) ← Rd(n+1), Rd(7) ← 0	Z,C,N,V	1
ROL	Rd	Rotate Left through Carry	Rd(0) ← C, Rd(n+1) ← Rd(n), C ← Rd(7)	Z,C,N,V	1
ROR	Rd	Rotate Right through Carry	Rd(7) ← C, Rd(n) ← Rd(n+1), C ← Rd(0)	Z,C,N,V	1
ASR	Rd	Arithmetic Shift Right	Rd(n) ← Rd(n+1), n = 0..6	Z,C,N,V	1
SWAP	Rd	Swap Nibbles	Rd(3..0) ← Rd(7..4), Rd(7..4) ← Rd(3..0)	None	1
BSET	s	Flag Set	SREG(s) ← 1	SREG(s)	1
BCLR	s	Flag Clear	SREG(s) ← 0	SREG(s)	1
BST	Rr, b	Bit Store from Register to T	T ← Rr(b)	T	1
BLD	Rd, b	Bit Load from T to Register	Rd(b) ← T	None	1
SEC		Set Carry	C ← 1	C	1
CLC		Clear Carry	C ← 0	C	1
SEN		Set Negative Flag	N ← 1	N	1
CLN		Clear Negative Flag	N ← 0	N	1
SEZ		Set Zero Flag	Z ← 1	Z	1
CLZ		Clear Zero Flag	Z ← 0	Z	1
SEI		Global Interrupt Enable	I ← 1	I	1
CLI		Global Interrupt Disable	I ← 0	I	1
SES		Set Signed Test Flag	S ← 1	S	1
CLS		Clear Signed Test Flag	S ← 0	S	1
SEV		Set Two's Complement Overflow	V ← 1	V	1
CLV		Clear Two's Complement Overflow	V ← 0	V	1
SET		Set T in SREG	T ← 1	T	1
CLT		Clear T in SREG	T ← 0	T	1
SEH		Set Half-carry Flag in SREG	H ← 1	H	1
CLH		Clear Half-carry Flag in SREG	H ← 0	H	1
NOP		No Operation		None	1
SLEEP		Sleep	(see specific descr. for Sleep function)	None	1
WDR		Watchdog Reset	(see specific descr. for WDR/Timer)	None	1

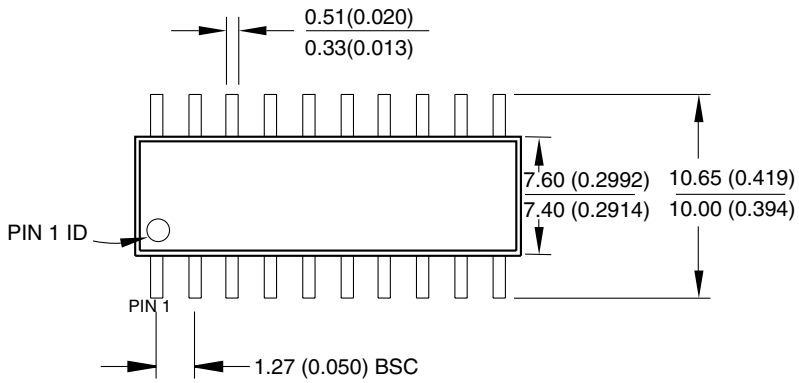
Ordering Information

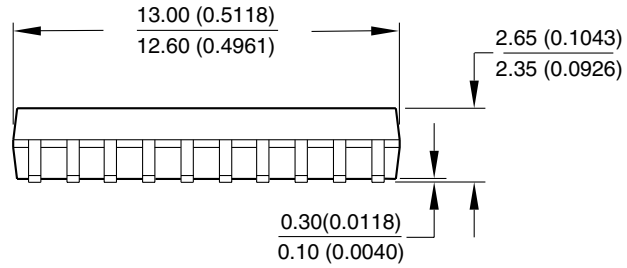
Speed (MHz)	Power Supply	Ordering Code	Package	Operation Range
4	2.7 - 6.0V	AT90S2313-4PC AT90S2313-4SC	20P3 20S	Commercial (0°C to 70°C)
		AT90S2313-4PI AT90S2313-4SI	20P3 20S	Industrial (-40°C to 85°C)
10	4.0 - 6.0V	AT90S2313-10PC AT90S2313-10SC	20P3 20S	Commercial (0°C to 70°C)
		AT90S2313-10PI AT90S2313-10SI	20P3 20S	Industrial (-40°C to 85°C)

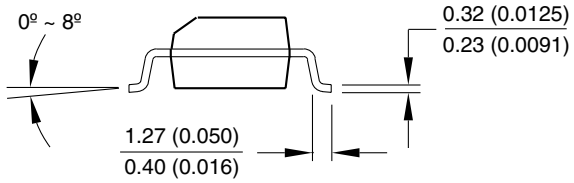
Package Type	
20P3	20-lead, 0.300" Wide, Plastic Dual Inline Package (PDIP)
20S	20-lead, 0.300" Wide, Plastic Gull Wing Small Outline (SOIC)

20S

20S, 20-lead, Plastic Gull Wing Small Outline (SOIC), 0.300" body.
Dimensions in Millineters and (Inches)*
JEDEC STANDARD MS-013







*Controlling dimension: Inches

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